L Number	Hits	Search Text	DB	Time stamp
1	5	"6140688"	USPAT	2002/08/01 08:51
2	923	((conduct$3 metal) near3 layer) with work adj function	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/01 09:03
3	544	(((conduct$3 metal) near3 layer) with work adj function) and ((first second) with (metal work conduct$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/01 09:16
4	504	((((conduct$3 metal) near3 layer) with work adj function) and ((first second) with (metal work conduct$3))) and (oxide 'TiN' titanum tantalum'Pt' 'Al' 'TaN')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/01 09:23
5	474	(((((conduct$3 metal) near3 layer) with work adj function) and ((first second) with (metal work conduct$3))) and (oxide 'TiN' titanum tantalum'Pt' 'Al' 'TaN')) and (thick thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/01 09:24
6	123	((((((conduct$3 metal) near3 layer) with work adj function) and ((first second) with (metal work conduct$3))) and (oxide 'TiN' titanum tantalum'Pt' 'Al' 'TaN')) and (thick thickness)) and ((thick thickness) with work adj function)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/01 09:26
7	69	(((((((conduct$3 metal) near3 layer) with work adj function) and ((first second) with (metal work conduct$3))) and (oxide 'TiN' titanum tantalum'Pt' 'Al' 'TaN')) and (thick thickness)) and ((thick thickness) with work adj function)) and (transistor gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/01 09:33
8	69	((((((((conduct$3 metal) near3 layer) with work adj function) and ((first second) with (metal work conduct$3))) and (oxide 'TiN' titanum tantalum'Pt' 'Al' 'TaN')) and (thick thickness)) and ((thick thickness) with work adj function)) and (transistor gate)) and work adj function	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/01 09:33

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L1: (5) "6140688"
L2: (923) ((conduct$3 metal) near3 layer) with work adj functic
L3: (544) 2 and ((first second) with (metal work conduct$3))
L4: (504) 3 and (oxide 'TiN' titanium tantalum'Pt' 'Al' 'TaN')
L5: (474) 4 and (thick thickness)
L6: (123) 5 and ((thick thickness) with work adj function)
L7: (69) 6 and (transistor gate)
L8: (69) 7 and work adj function

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DBs | USPAT; US-PGPUB; EPO; JPO; DERWENT; II | Plurals

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7 and work adj function

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2	☐	☐	US 20020089477 A1	20020711	22	Display apparatus, display apparatus driving method, and liquid crystal dis	345/87	
3	☐	☐	US 20020061646 A1	20020523	13	Embedded metal nanocrystals	438/660	
4	☐	☐	US 20020057050 A1	20020516	87	Organic light emitting diode devices using aromatic amine compounds wit	313/504	430/58.15; 430/58.5;
5	☐	☐	US 20020055319 A1	20020509	31	Low gate current field emitter cell and array with vertical thin-film-edge emitt	445/24	
6	☐	☐	US 20020042241 A1	20020411	32	Low gate current field emitter cell and array with vertical thin-film-edge emitt	445/24	
7	☐	☐	US 20020039730 A1	20020404	10	Organic electroluminescent device and manufacturing method therefor	435/6	
8	☐	☐	US 20020036291 A1	20020328	21	Multilayer structures as stable hole-injecting electrodes for use in hig	257/72	
9	☐	☐	US 20020021088 A1	20020221	22	Organic light emitting diode devices with improved anode stability	313/504	313/506
10	☐	☐	US 20020021068 A1	20020221	9	E-M WAVE GENERATION USING COLD ELECTRON EMISSION	313/231.61	

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